

VERSION TO SHOW CHANGES MADE

IN THE CLAIMS:

Claims 3-6 have been canceled.

The claims have been amended as follows:

2. (Twice Amended) An insulated gate transistor having a gate electrode on a substrate with a gate insulator interposed therebetween, wherein the gate insulator including silicon and oxygen contains both nitrogen atoms and [halogen] fluorine atoms, and wherein nitrogen atom concentration of the gate insulator is [not less] more than $1 \times 10^{20} \text{ cm}^{-3}$.

Claims 13-23 have been added.